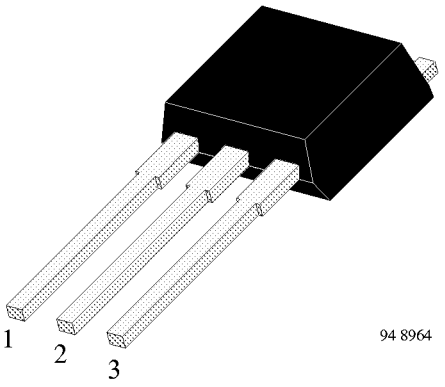
Silicon NPN High Voltage Switching Transistor

Features

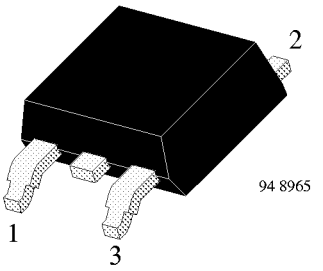
- Monolithic integrated C-E-free-wheel diode
- Simple-sWitch-Off Transistor (SWOT)
- HIGH SPEED technology
- Planar passivation
- 100 kHz switching rate
- Very low switching losses
- Very low dynamic saturation
- Very low operating temperature
- Optimized RBSOA
- High reverse voltage

Applications

Electronic lamp ballast circuits



BUD700D
1 Base 2 Collector 3 Emitter



BUD700D –SMD
1 Base 2 Collector 3 Emitter

Absolute Maximum Ratings

T_{case} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Collector-emitter voltage		V_{CEO}	400	V
		V_{CEW}	500	V
		V_{CES}	700	V
Emitter-base voltage		V_{EBO}	11	V
Collector current		I_C	2	A
Collector peak current		I_{CM}	3	A
Base current		I_B	0.75	A
Base peak current		I_{BM}	1	A
Total power dissipation	$T_{case} \leq 50°C$	P_{tot}	20	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	–65 to +150	°C

Maximum Thermal Resistance

T_{case} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Junction case		R_{thJC}	5	K/W

Electrical Characteristics

T_{case} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Transistor						
Collector cut-off current	V_{CE} = 700 V	I_{CES}			50	µA
	V_{CE} = 700 V; T_{case} = 150°C	I_{CES}			0.5	mA
Collector-emitter breakdown voltage (figure 1)	I_C = 300 mA; L = 125 mH; $I_{measure}$ = 100 mA	$V_{(BR)CEO}$	400			V
Emitter-base breakdown voltage	I_E = 1 mA	$V_{(BR)EBO}$	11			V
Collector-emitter saturation voltage	I_C = 0.3 A; I_B = 0.1 A	V_{CEsat}		0.1	0.2	V
Base-emitter saturation voltage	I_C = 0.3 A; I_B = 0.1 A	V_{BEsat}		0.9	1	V
DC forward current transfer ratio	V_{CE} = 2 V; I_C = 10 mA	h_{FE}	10			
	V_{CE} = 2 V; I_C = 0.3 A	h_{FE}	10			
	V_{CE} = 5 V; I_C = 2 A	h_{FE}	4	6		
Collector-emitter working voltage	V_S = 50 V; L = 1 mH; I_C = 2 A; I_{B1} = 0.7 A; $-I_{B2}$ = 0.2 A; $-V_{BB}$ = 5 V	V_{CEW}	500			V
Dynamic saturation voltage	I_C = 1 A; I_B = 0.2 A; t = 1 µs	$V_{CEsatdyn}$			15	V
	I_C = 1 A; I_B = 0.2 A; t = 3 µs	$V_{CEsatdyn}$			4	V
Gain bandwidth product	I_C = 200 mA; V_{CE} = 10 V; f = 1 MHz	f_T	4			MHz
Free-wheel diode						
Forward voltage	I_F = 0.7 A	V_F			1.2	V

Switching Characteristics

T_{case} = 25°C, unless otherwise specified

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Application specific switching time						
measured with Nylos3		t_x			0.75	µs
Resistive load (figure 2)						
Turn on time	I_C = 330 mA; I_{B1} = 85 mA; $-I_{B2}$ = 170 mA; V_S = 250 V	t_{on}			0.25	µs
Storage time		t_s			3	µs
Fall time		t_f			0.4	µs

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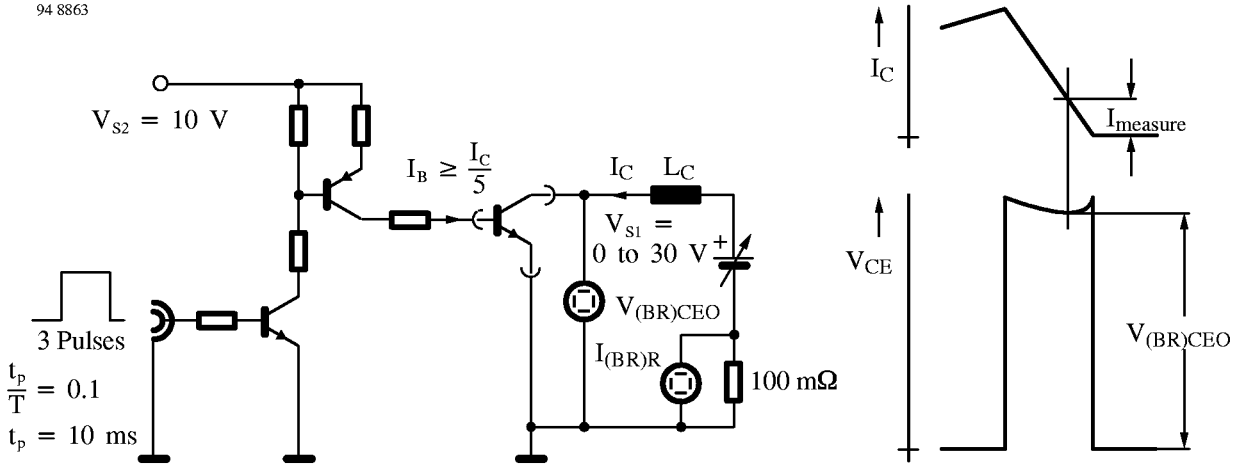

Figure 1. Test circuit for $V_{(BR)CE0}$

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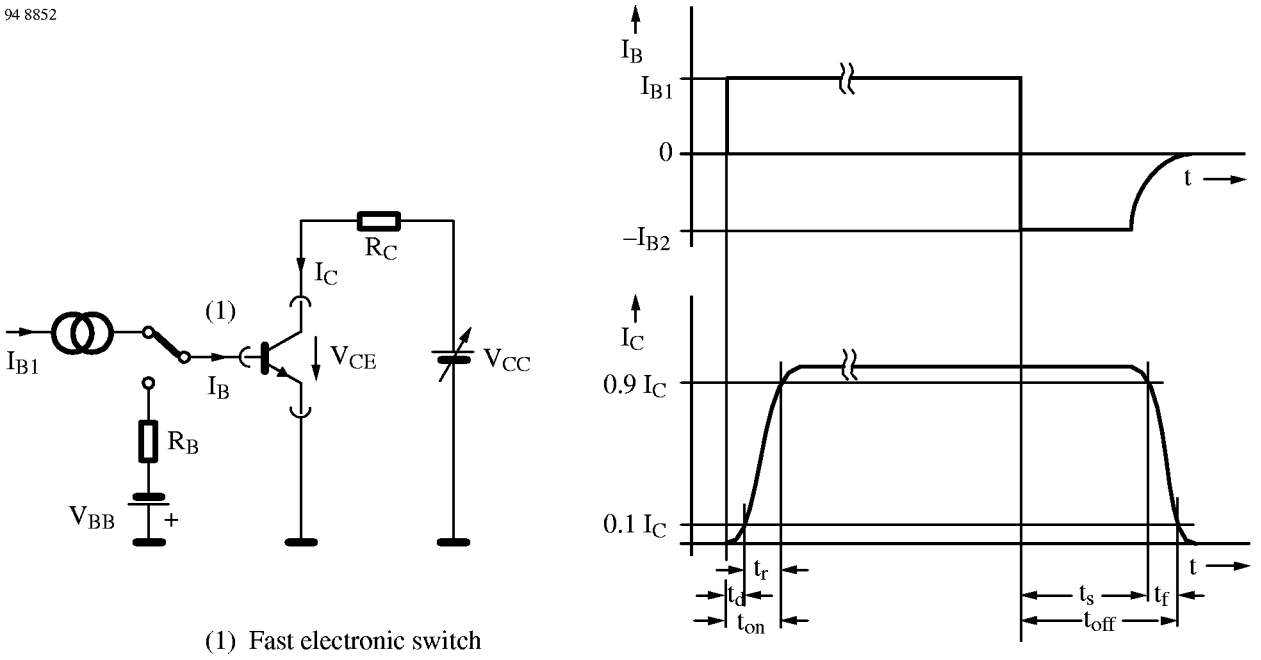


(1) Fast electronic switch

Figure 2. Test circuit for switching characteristics – resistive load

Typical Characteristics (T_{case} = 25_C unless otherwise specified)

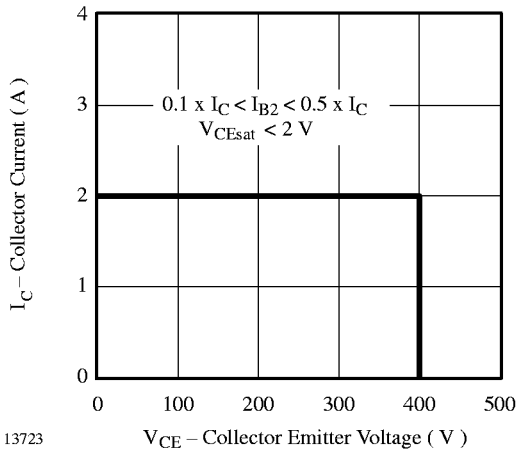


Figure 3. V_{CEW} – Diagram

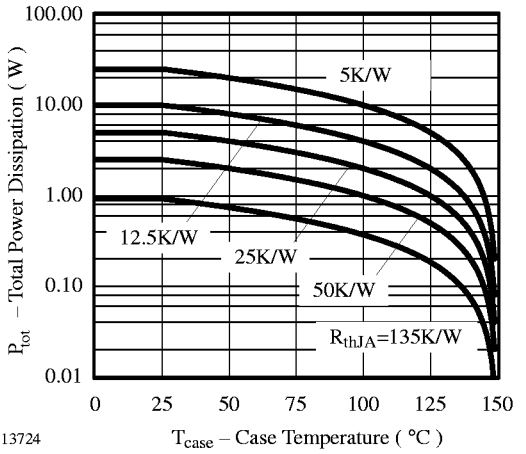


Figure 6. P_{tot} vs. T_{case}

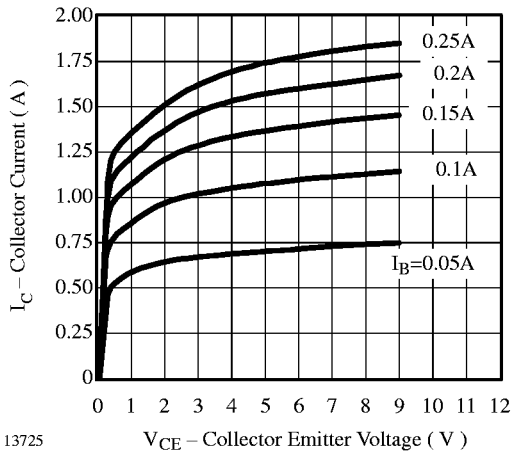


Figure 4. I_C vs. V_{CE}

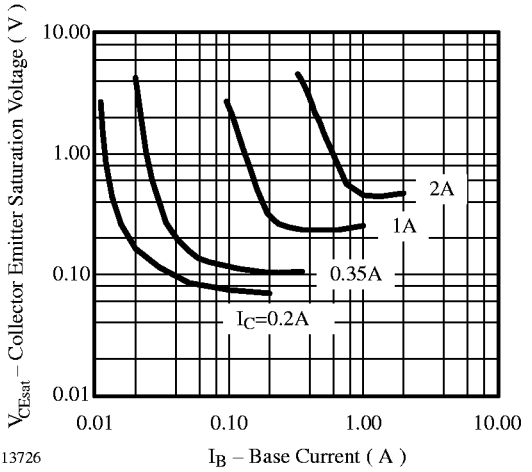


Figure 7. V_{CEsat} vs. I_B

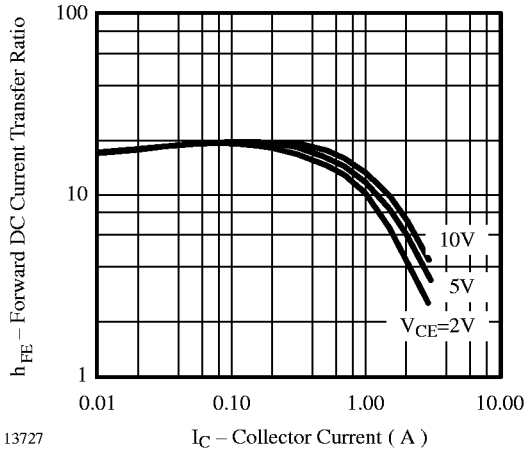


Figure 5. h_{FE} vs. I_C

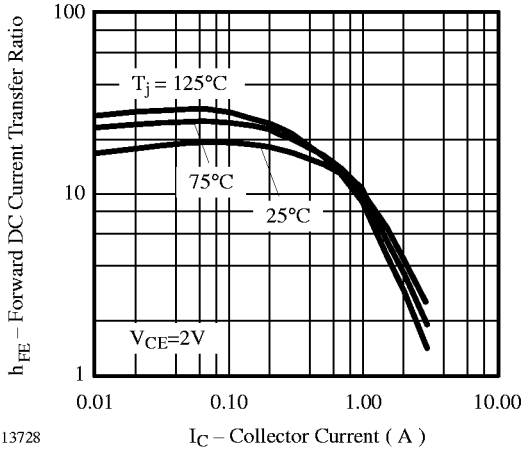


Figure 8. h_{FE} vs. I_C

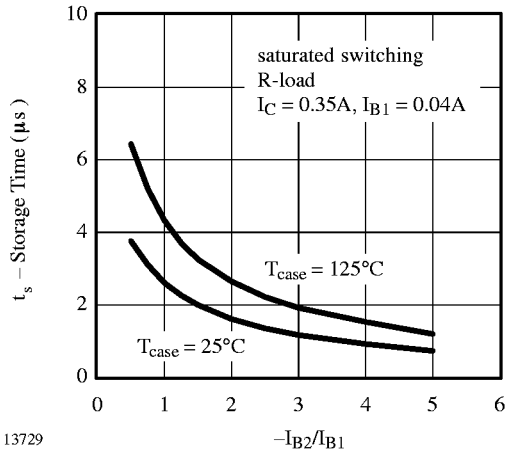


Figure 9. t_s vs. $-I_{B2}/I_{B1}$

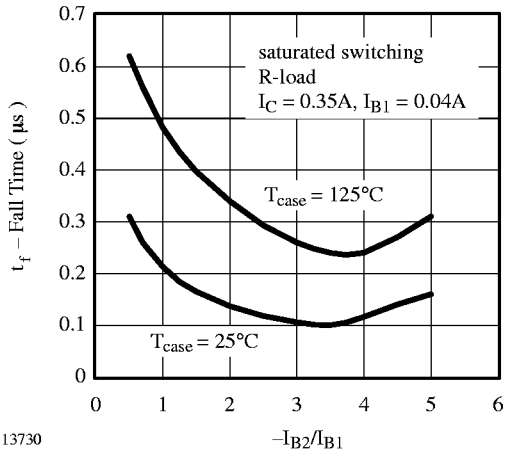


Figure 12. t_f vs. $-I_{B2}/I_{B1}$

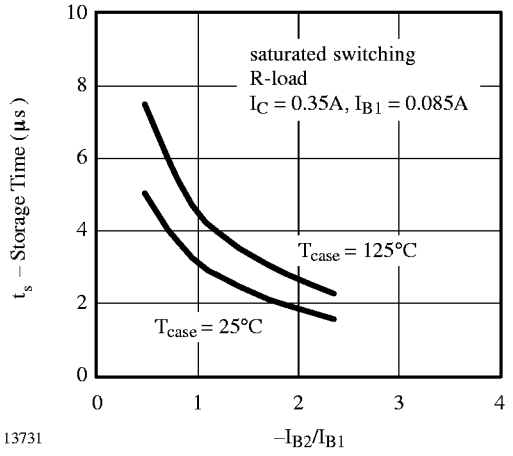


Figure 10. t_s vs. $-I_{B2}/I_{B1}$

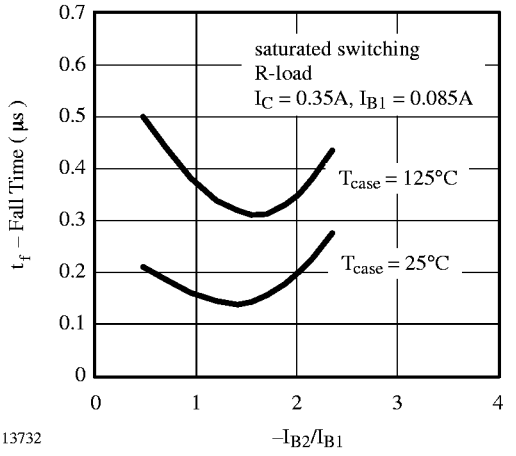


Figure 13. t_f vs. $-I_{B2}/I_{B1}$

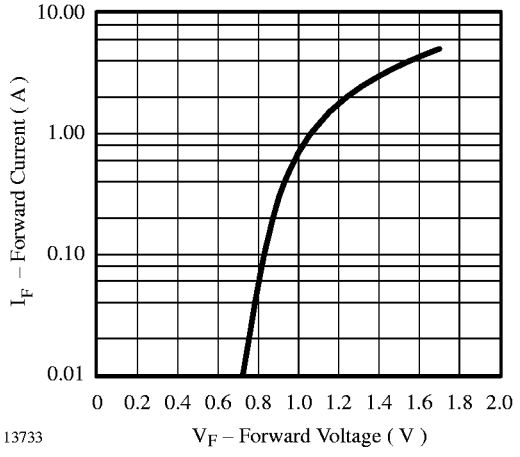
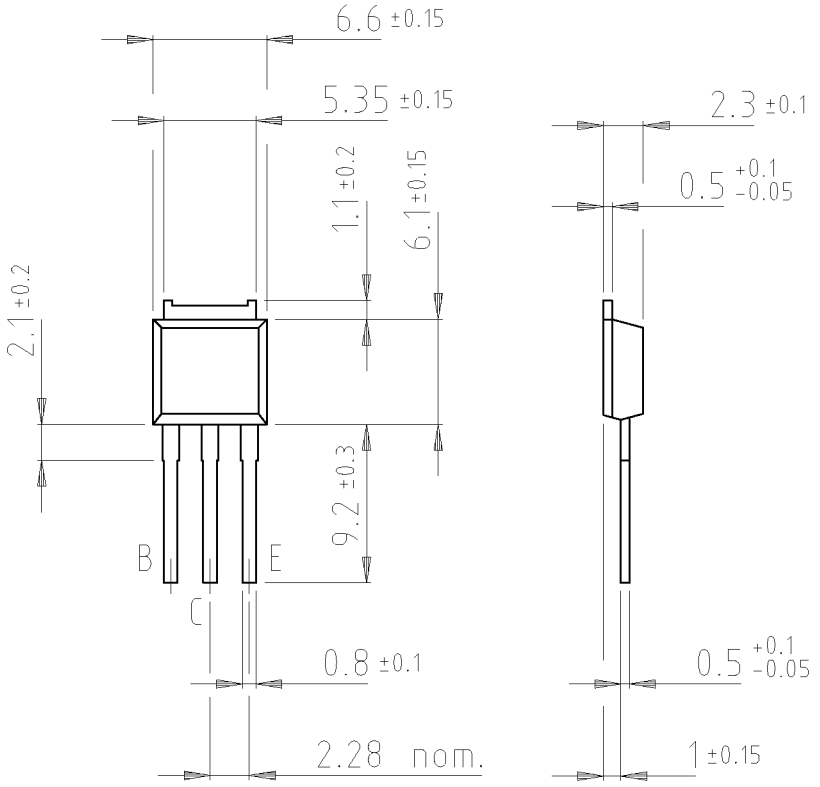


Figure 11. I_F vs. V_F

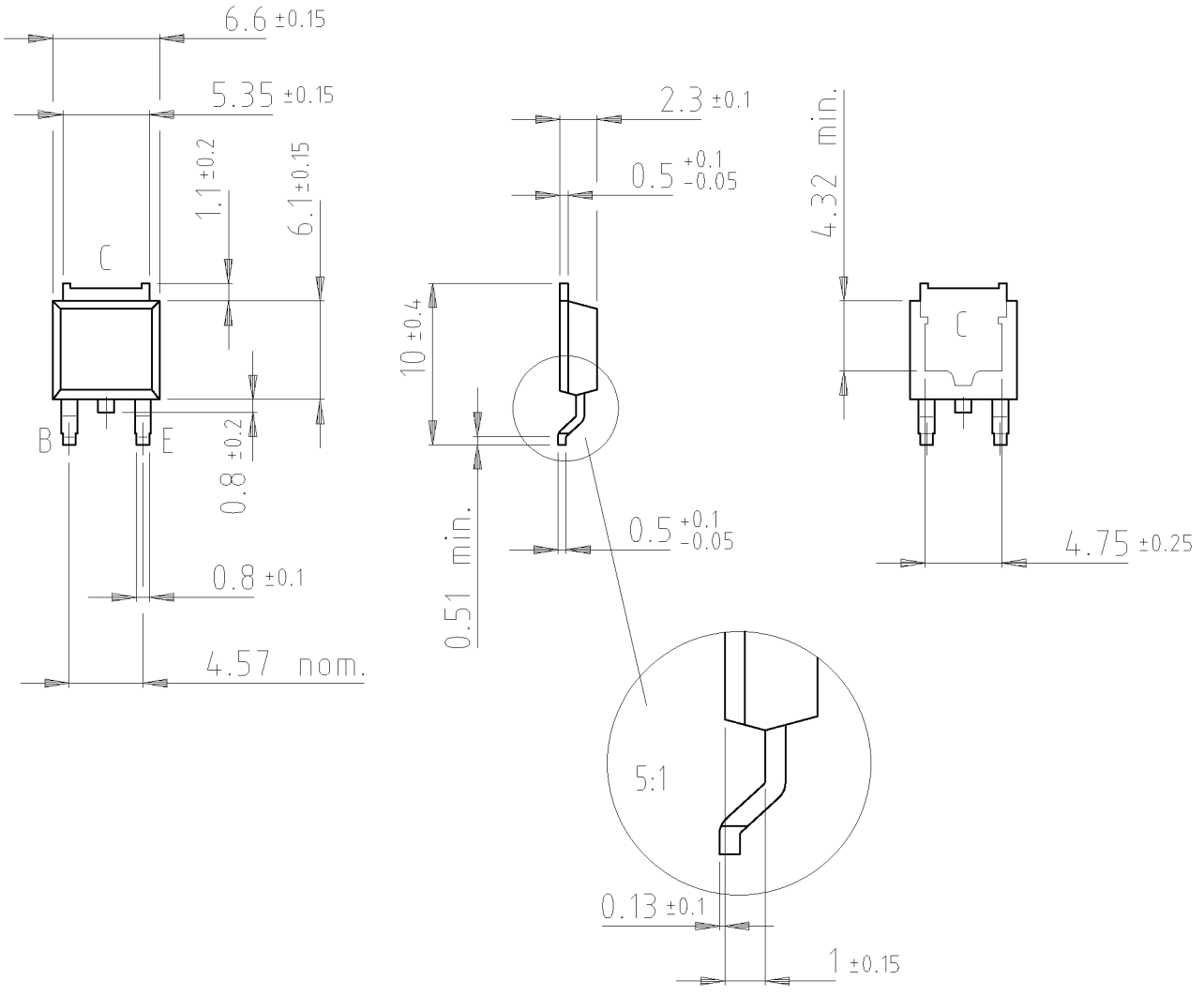
Dimensions in mm



technical drawings according to DIN specifications

Plastic case JEDEC TO 251
Collector connected with metallic surface

14292



Plastic case JEDEC TO 252
Collector connected with metallic surface

14293

technical drawings
according to DIN
specifications

For ordering TO 252 add SMD to the type number (i.e. BUD700D –SMD)